KMIP3-C425NS

Description

KMIP3-C425NC is InGaAs PIN Photodiode with □ 250 um active area in Φ3.0mm ceramic pkage.
It is recommended for optical data communication and power monitoring.

Features

- Front illuminated planar PIN-PD
- Low capacitance and low dark current
- Ceramic pkage with Φ3.0mm resine dome.
- High reliability and environmental endurance
- Wide operating wavelength range from 1.1mm to 1.6mm

Applications

- Optical Data Communications
- Optical power monitoring

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Reverse Voltage	V_R	20	V
Maximun Optical Power Input	P_{max}	30	mW
Forward Current	I_F	50	mA
Operating Temperature	T_{opr}	-40 ~ +85	℃
Storage Temperature	$T_{stg.}$	-40 ~ +100	℃
Soldering Temperature *1	$T_{sol.}$	260	℃

**1 : Soldering Time ≤ 10 seconds (at a distance of 1mm from the package)*

Electro-Optical Characteristics

Parameter		Symbol	Min.	Typ.	Max.	Unit	Condition
Active area		D		□ 250		㎛	
Dark Current		I_D			1.0	nA	@ V_R=5V, 25℃
Responsivity	1.31um	S	0.85			mA/mW	@ V_R=5V, 25℃
	1.55um		0.90				
3dB Cut off frequency		BW		0.6	-	GHz	@V_R=5, RL=50Ω
Capacitance		Cp		5	8	pF	@ V_R=5V, f=1MHz

* These specifications are subject to change without notice.

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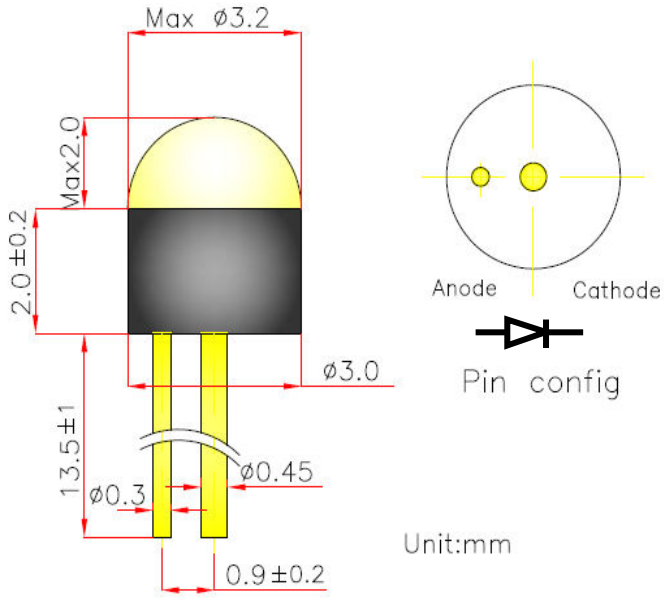
Outline Drawing



Ordering information

KMIP	Pin type -	PKG Method	PKG type	Active Size	Pin Config.
KODENSHI Mini CAN InGaAs PIN PD	1 : 1Pin	F : Cap with Flat Window	2 : Ø2	5: Ø50um	A:Cathod Common
	2 : 2Pin	B : Cap with Ball lens	3 : Ø2.96	8: Ø75um	B:Anode Common
	3 : 2Pin Isolated	L : Longcap with Ball lens	4 : Ø3.0	25: □250um	C:CASE GND
		C : Ceramic Dome			D:CASE Anode
					N: Normal

Available now

Lead Form'g
S : straight lead
C : center lead form
L : side lead form